

HSB276AS

Silicon Schottky Barrier Diode for Balanced Mixer

HITACHI

ADE-208-838(Z)

Rev. 0

Feb. 2000

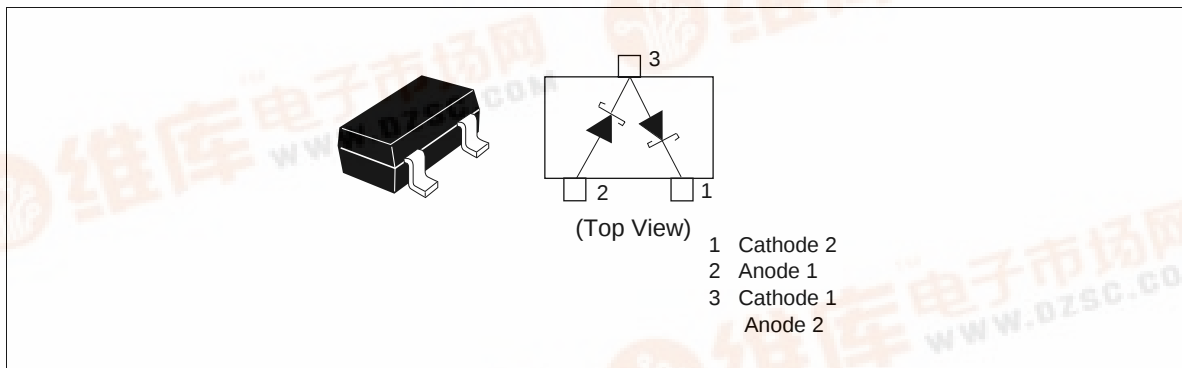
Features

- High forward current, Low capacitance.
- HSB276AS which is interconnected in series configuration is designed for balanced mixer use.
- CMPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSB276AS	E8	CMPAK

Outline



HSB276AS

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	5	V
Reverse voltage	V_R	3	V
Average rectified current	I_O^{*1}	30	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to +125	°C

Note 1. Per one device

Electrical Characteristics (Ta = 25°C) *2

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	V_R	3	—	—	V	$I_R = 1 \text{ mA}$
Reverse current	I_R	—	—	50	μA	$V_R = 0.5\text{V}$
Forward current	I_F	35	—	—	mA	$V_F = 0.5\text{V}$
Capacitance	C	—	—	0.90	pF	$V_R = 0.5\text{V}$, $f = 1 \text{ MHz}$
Capacitance deviation	ΔC	—	—	0.10	pF	$V_R = 0.5\text{V}$, $f = 1 \text{ MHz}$
ESD-Capability ^{*1}	—	30	—	—	V	C = 200pF , R = 0 Ω Both forward and reverse direction 1 pulse.

Note 1. Failure criterion ; $I_R \geq 100\mu\text{A}$ at $V_R = 0.5 \text{ V}$

Note 2. Per one device

Main Characteristic

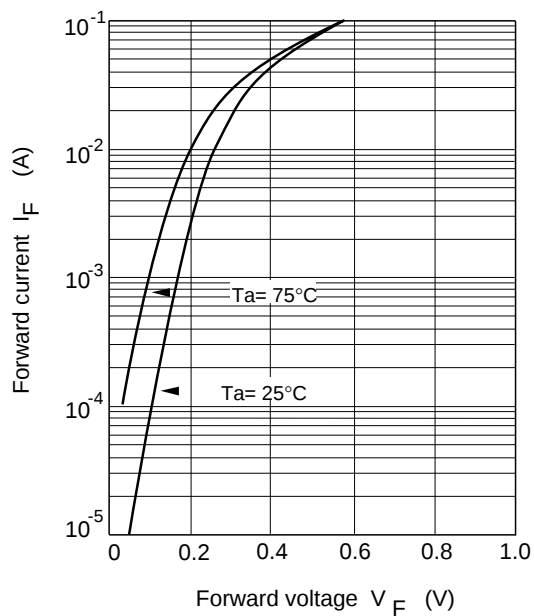


Fig.1 Forward current Vs. Forward voltage

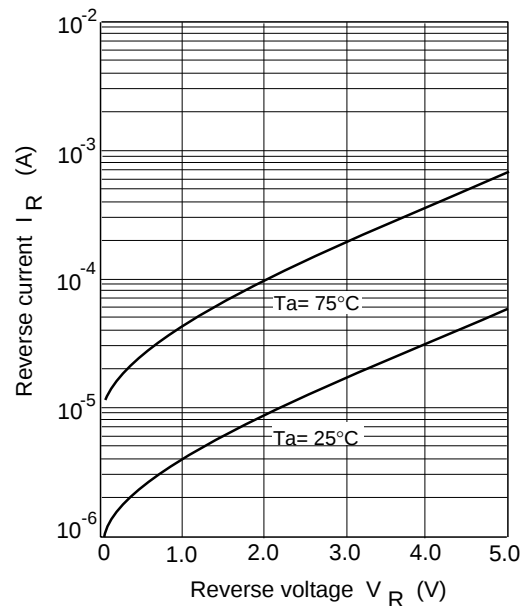


Fig.2 Reverse current Vs. Reverse voltage

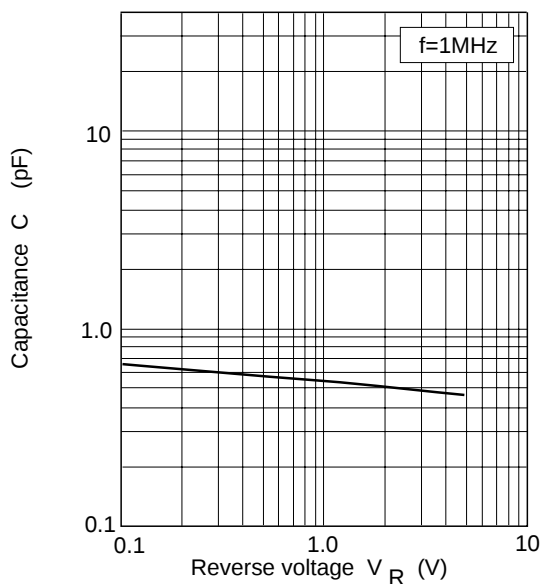
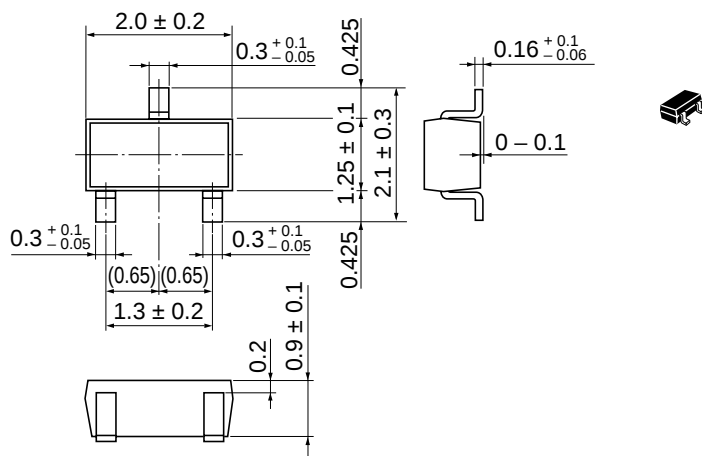


Fig.3 Capacitance Vs. Reverse voltage

HSB276AS

Package Dimensions

Unit: mm



Hitachi Code	CMPAK
JEDEC	—
EIAJ	Conforms
Mass	0.006 g

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL NorthAmerica : <http://semiconductor.hitachi.com/>
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Domacher StraÙe 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX